Index

1-μm YAG laser, (Nd:YAG laser) 6, 9, 28, 29, 30, 32, 35, 41, 45, 73, 113, 115, 122, 134, 157, 159, 164, 175, 185, 284, 291, 362, 525, 931
  frequency doubled, 708, 709
2-μm thulium laser, 11, 18, 135, 137, 138, 525, 934
  Tm:YAG laser, 936, 1004, 1016
3D tomography, 53
6.7-nm neon operation, 342
193-nm solid-state laser, 14

Abel inversion, 286, 661
ablation effect, 1087, 1099
ablation imprints, 613
ablation pattern, 617
ablation threshold, 265, 607, 612
absolutely calibrated in-band energy measurements, 511
absorption coefficient, 5, 77, 90, 97, 132, 154, 156, 167, 565, 641
absorption spectroscopy, 640, 890
absorption coefficient for IBA, 5
absorption edge, 339, 387, 597, 688, 728
absorption spectra, 642, 890
accelerators and compact storage rings for lithography and metrology, 1036, 1040
acoustic intensity, 836
acoustic wave, 662, 837, 874, 877, 921
actinic in-band mapping EUV reflectometry (AIMER™), 456
actinic mask-blank inspection (ABI), 9
actinic metrology tools, 14, 714
actinic patterned-mask inspection (APMI), 8, 13, 714
active materials for laser pulse generation, 931
active mirror, 951, 1002
active mode locking, 271
adaptive mesh refinement (AMR), 86, 102
adhesive-free bonding, 955
adjustable-phase undulator (APU), 1095
Adlyte AG, 10
Advanced Light Source (ALS), 414, 458, 679, 715, 918, 1135
Aerial Image Metrology System (AIMS™), 9, 358, 359, 374, 541, 714, 919, 1045
AIXUV, 416, 417
ALE–AMR code, 102
all-normal dispersion (ANDi), 967
amorphous carbon (a-C), 608, 616
amplified spontaneous emission (ASE), 212, 265, 618, 820, 913, 916, 927, 930, 967, 1002, 1056, 1067
amplifier function, 781
anamorphic beam expansion, 828
angle of acceptance, 17, 566

anode, 350, 354, 360, 364, 384, 391, 416, 419, 427, 449, 808, 815, 1111, 1116, 1122, 1123
anomalous transmission, 510, 514, 516
anomalous transmission filter, 514, 516
arbitrary Lagrange–Eulerian (ALE) technique, 85
arc sections, 1078, 1083
ArF excimer laser, 796, 803, 804, 813, 826, 828, 1066
ArF immersion, 257, 803, 805
argon, 342, 351, 388, 389, 390, 398, 404, 417, 433, 634, 640, 756, 760, 794, 851, 856, 1113
atomic diffusion bonding (ADB), 955
atomic opacity, 115, 120, 121, 122, 123, 134, 139
atomic process timescales, 91, 92
atomic scattering factors, 565
Atomic Spectra Database, 437
atomic tin data, 1195
atomic xenon data, 1129
attenuation length, 53, 612, 615
attosecond pulses, 886, 889, 918
automated endpoint detection, 494
average charge state, 32, 125, 127, 131
average ion charge, 5, 74
axial cooling, 951
AXUV diodes, 696, 702, 703

B-integral, 913, 921, 925, 954,1006
back focal length, 542
back-illuminated CCD, 354, 453, 517, 521
back-reflection, 279, 302, 487, 617
backlighting images, 630
BaF_2, 820
bandwidth control module (BCM), 835, 839
BBO crystals, 960, 968, 970
beam characterization, 604, 614
beam expander, 278, 797
beam imprinting, 612
beam quality, 48, 211, 268, 290, 854, 862, 888, 914, 922, 938, 944, 1001, 1011, 1084, 1097
Beamline 2 at SURF III, 681, 682
Beamline 3 at SURF III, 682
bending magnets, 679, 1039, 1040, 1050, 1052, 1055, 1081, 1084
Bennet's equation, 11
Berkeley Actinic Inspection Tool, 715
BESSY II, 515, 519, 679, 683, 697
"beyond EUV" (BEUV), 17, 43, 1097
bias gas, 423, 447, 449
bifurcation, 945
big-aperture thulium (BAT)
  architecture and design, 1011
  laser concept, 1000
  lasers, 18, 1013
Blue-X, 15, 18, 47, 50, 1097
Boltzmann plot, 640
bound state populations, 75
Bragg condition, 514
Bragg reflectors, 510
breakdown voltage, 385, 418, 816, 1118, 1119
bremsstrahlung, 90, 481, 487
  inverse, 5, 31, 32, 76, 77, 81, 89, 167, 180, 481, 482
brightness, 8, 15, 30, 134, 335, 351, 366, 484, 485, 496, 605, 919, 1029, 1031, 1048, 1076
broadband plasma source, 15, 16
broadband radiation source, 482, 496, 688, 728
broadband spectroscopy, 510
broadband UV–visible radiation, 15
buffer gas, 231, 234, 236, 239, 241, 243, 310, 398, 668, 755, 757, 767, 798, 823, 1118

bunch charge, 1077, 1080
bunch compression, 1083, 1086
bunch length, 1051, 1076, 1080, 1083
bunch repetition frequency, 1079, 1082, 1086
burst mode, 306, 829, 961, 965

CaF_2, 820, 923, 934
calibration, 498, 681, 703, 705, 861
cap layer, 552
catadioptric design, 819, 820
cathode, 350, 354, 360, 364, 383, 392, 417, 449, 482, 489, 808, 1075, 1111, 1120, 1197
  hollow, 12, 416
cathode spot, 489
cavity dumping, 939, 943
Center for X-Ray Optics (CXRO), 235, 334, 341, 565, 679, 863
central wavelength (CWL_{50}), 7, 210, 262, 455, 456, 515, 517, 522, 809, 933, 974, 1004
ceramic insulator, 415
charge-state distribution (CSD), 125
charging time, 816
chirp rate, 273, 967
chirped Bragg gratings, 947
chirped mirrors, 942, 947, 958
chirped-pulse amplification (CPA), 925, 946, 952, 958, 973, 977
chromatic aberration, 264, 339, 797, 809, 819
chromatic dispersion, 946
circuit inductance, 818
CIV3 (atomic code), 1196
clean dry air (CDA), 417
clearance ratio (CR), 814
closed-loop control, 421, 444, 1039
CO_2 amplifiers, 211, 779, 786
CO_2 gas lasers, 11, 134
CO_2 lasers with transverse-gas-flow, 780
Code Comparison workshop, 13
coherent beam combining, 950
coherent diffractive imaging (CD), 867
coherent EUV light sources based on high-order harmonic generation, 847
coherent EUV-scattering microscope (CSM), 721, 724
coherent EUV source, 918
coherent scattering microscope with *in situ* accelerated contamination system, 724
coherent synchrotron radiation (CSR), 1084
cohesive energy, 605
collection efficiency, 206, 265, 305, 388, 401, 695, 704, 712, 914
collective scattering, 662
collector
  ellipsoidal, 204, 209, 227, 228, 305, 541, 545, 578, 636
  paraboloidal, 633, 643
collector contamination, 748, 758
collector lifetime, 11, 231, 235, 310, 373, 400, 558, 757, 769
collector mirror, 228, 245, 310, 426, 540, 557, 697, 699
collector module, 402, 554
collector optics, 28, 201, 208, 263, 373, 405, 538, 555, 672, 681, 698
collision frequency, 76, 77, 156, 659
collisional–radiative (CR) equilibrium, 31, 43
collisional–radiative (CR) modeling, 32, 124
collisional rate, 91, 124, 126
COLTRIMS, 890
complex reflectivity coefficient, 564
Compton scattering, 919, 952
configuration-averaged calculation, 93

configuration interaction (CI), 117, 125, 1133, 1197
configuration interaction (CI) convergence, 117, 120
configuration-mixing approximation, 1196
contact exposure, 1124
contamination, 224, 239, 308, 382, 429, 511, 540, 555, 612, 685, 688, 700, 710, 724, 748, 758, 821, 861, 883, 915
contamination damage, 612
contamination growth process, 710
continuous optical discharge, 477
continuum hypothesis, 84
convective flow, 490
conversion efficiency (CE), 11, 28, 29, 96, 113, 136, 150, 175, 184, 185, 203, 206, 210, 226, 261, 309, 334, 358, 362, 367, 375, 385, 389, 391, 417, 437, 443, 497, 525, 556, 656, 694, 850, 854, 855, 857, 914, 918, 999, 1016, 1067
  of laser photons to EUV photons, 18
  steady-state theoretical maximum, 185, 187
  wall-plug to photon, 11
convolved spectral bandwidth, 824
cost of ownership (CoO), 209, 480, 699, 805, 1040, 1044
Coulomb logarithm, 6, 75, 90, 168, 181
Courant condition, 84, 85, 100
crater profiles, 614
critical angle, 564, 604, 608
critical-dimension, error, 839, 479, 493, 496
critical (electron) density, 6, 33, 41, 73, 75, 78, 82, 121, 134, 150, 180, 203, 656, 848
critical ionization level, 854
cross-flow fan (CFF), 814
cross-relaxation process, 935, 936
cutoff rule, 853
cyberspace, 778

damage pattern, 604
damage threshold, 278, 595, 609, 913, 926, 933, 946
DC photocathode gun, 1079
Debye length, 31, 74, 84, 428, 662
debris management, 758, 764
debris mitigation, 9, 30, 227, 233, 241, 267, 280, 310, 351, 372, 398, 423, 425, 450, 557, 748, 754, 769
  magnetic, 10
debris mitigation buffer gas, 755
debris (mitigation) shield, 350, 367
deconvolution, 389, 829
deconvolved spectral bandwidths, 812, 825
deep UV (DUV), 7, 206, 208, 229, 262, 478, 497, 524, 548, 688, 705, 714, 748, 795, 803, 840
deflecting charged particles, 426
depth of focus, 53, 795, 883
desorption, 605, 607, 612, 1038, 1053
desorption printing, 614
desorption/ablation model, 607
diagnostic etalon, 811
dielectric constant, 76, 879
dielectronic recombination, 31, 645, 1133, 1135
diffraction efficiency, 519, 521, 527, 683, 860, 873, 974
diffraction-limited beam, 938, 959
diffraction-limited storage ring (DLSR), 1032, 1036
diffraction order, 520, 680, 694, 727
diffusion limit, 154
Digital Signal Registration, 443
digitalization, 778

diode pumping, 928, 931, 934, 937, 1001
dioptric design, 819
discharge chamber, 665, 798, 826
discharge circuit parameters, 796
discharge head, 423, 424
discharge lamp, 1107
discharge-produced EUV source, 416
discharge-produced plasma (DPP), 11, 203, 256, 367, 374, 382, 405, 416, 478, 510, 521, 539, 755
discrete ordinates (S_N), 97, 101
disk target, 225, 270, 309, 525
dissociation, 238, 281, 302, 312, 628, 635, 642, 759, 890, 921
distribution function, 75, 81, 91, 95, 124, 662, 667
dome targets, 270
Doppler broadening, 438, 662
dose–contrast curve, 452, 886
dose control, 244, 301, 450, 510, 808
dose stability, 200, 202, 210, 245, 293, 298, 301, 796, 830, 838
double-laser ignition, 360, 362, 364
DPP EUV sources, 416
drift velocity, 661
drive laser, 11, 18, 54, 101, 113, 134, 200, 209, 213, 216, 226, 271, 284, 296, 304, 521, 525, 528, 540, 547, 553, 660, 999
droplet position stability, 267, 288
Drude model, 659
dump line, 1078, 1087
dumping speed, 798
durability assessment, 604
duty cycle, 7, 9, 17, 206, 209, 226, 294, 310, 359, 386, 422, 708, 1045, 1056
DUV lithography, 263, 748, 803
dynamic aperture, 1039, 1050
dynamic gas lock (DGL), 7, 243, 426, 431
E95 value, 837, 839
E-CAM, 432, 445
edge placement error (EPE), 16, 496
edge pumping, 950
effective area, 586, 611
effective plasma temperature, 121, 525
effective reflectance (R_{eff}), 458
effective temperature, 129, 137
elastic tensor, 879
electrode erosion, 12, 351, 375, 39, 405
electrode lifetime, 374, 425, 450
electromagnetic pump, 355
electron beam, 14, 415, 519, 679, 794, 1031, 1041, 1068, 1097, 1134
electron bean ion trap (EBIT), 1134, 1136
electron beam photoresist, 886
electron bunch, 606, 916, 1044, 1051, 1069, 1085
electron density, 6, 31, 75, 121, 177, 270, 361, 387, 628, 647, 656, 659, 665
electron diagnostics, 659
electron–electron collisions, 80, 82
electron gun, 1075, 1078
electron–hole pair, 702
electron impact ionization cross-section, 41
electron–ion collisions, 74, 82, 154
electron plasma frequency, 6, 659
electron storage ring, 678, 684, 1035, 1042, 1047, 1076
electron temperature, 6, 12, 29, 42, 81, 124, 168, 204, 270, 344, 361, 382, 640, 655, 765
electron velocity distribution function, 662
electro-optic switch, 968
electro-optical modulation, 271
electrostatic analyzer, 671

ellipsoidal mirror, 209, 306, 510, 547, 567, 573, 577, 594, 633
emission coefficient, 89, 1011
emission cross-section, 923, 931, 1004, 1010, 1014
emission profile, 388, 661
emission spectroscopy, 635
emission wavelength, 491, 923, 928, 932, 967, 977
emissivity, 94, 120, 285, 401,1122, 1202
  EUV, 664
emittance, 680, 917, 1031, 1048, 1051, 1072, 1079
E-Mon™ energy meter, 424, 725
endpoint detection for etching, 493
  CVD and CMP processes, 494
end pumping, 929, 948
energy extraction efficiency, 275, 944
energy instability, 945
energy level diagram, 116, 1008, 1110
energy-recovery linac (ERL), 1068, 1075
energy spectra, 668
ensemble simulations, 104
epoxy bonding, 955
equation of state (EOS), 84, 152
  Frankfurt EOS (FEOS) model, 155
equilibration timescales, 81
ERL-FEL, 1068, 1076
E-SPEC, 432, 731
etalon, 797, 811
étendue, 7, 8, 9, 17, 28, 53, 202, 206, 263, 333, 358, 401, 482, 541, 1045
Euler equations, 84
Eulerian method, 85
European XFEL, 615
EUV-Lamp, 413
EUV applications, 13, 369, 541, 782
EUV microscope (EUVM), 715, 721
EUV source requirements, 7, 9, 204, 358
  étendue of source output, 7
  EUV power (in-band), 7
  integrated energy stability, 7
  maximum solid angle input to illuminator [sr], 7
  reflectivity degradation, 7
  repetition frequency, 7
  source cleanliness, 7
  spectral purity, 7
EUV/x-ray sources, 605, 608
excimer lasers, ArF and KrF, 778, 794, 796
  line-narrowed, 821, 826
exciplex, 794
excited dimer, 794
excited-state distribution, 92
explicit method, 84
extreme-ultraviolet (EUV)
  ablation, 614
  brightness, 30, 362, 366, 369, 374
  collector optics, 539, 672
  dose control, 244
  emission waveform, 359
  FEL beam, 608, 614
  exposure, 256, 287, 450, 521, 647, 885
  induced chemical dynamics, 888
  induced plasmas for materials treatment, 647
  interference lithography for resist characterization, 883
  laser, 607, 612, 616, 848, 1055
  laser beams, 612
  metrology sources, 15
  optical elements, 604, 610
  optical train, 537
  pellicle, 459, 460
  photon sources, 510, 517
  photon sources spectral characteristics, 521

plasma, 220, 261, 262, 285, 385, 645, 656, 669, 756, 758, 769
power/brightness metrology, 333
radiometry, 678, 684, 696
radiometry beamline at the MLS, 685, 687
reflectometer, 450, 699
resist exposer, 450
scanner sources, 7
source cleanliness, 7, 206, 372
source description and requirements, 6
source metrology, 122, 432, 509, 514, 679
Extreme-Ultraviolet Lithography System Development Association (EUVA), 257, 259

F_2 laser, 696, 805, 819, 825
F_2 lithography, 805, 819
fabrication threshold fluence, 595
far field, 228, 539, 543, 554, 720, 868, 1011
Faraday cups, 668
Faraday rotator, 960, 970
fast axial flow (FAF), 211, 275, 780
fast high-voltage discharge, 798
fast transverse flow (FTF), 211, 275, 780
feedback control, 265, 294, 358, 371, 808
FEL-induced surface structure, 617
FEL parameter, 1071, 1082, 1086
femtosecond oscillator, 952
femtosecond laser, 51, 594, 849, 872, 889, 934
femtosecond pulse generation, 913
Feshbach resonance, 891
fiber lasers, 478, 789, 938, 948, 978, 1002
fiber oscillator, 967
filters for spectroscopy from the soft x-ray to visible wavelength range, 520
FLASH (free-electron laser facility in Hamburg, Germany), 608
flashlamp pumping, 1000
Flexible Atomic Code (FAC), 1195
fluorescence lifetime, 923, 1009
fluorine gas, 798
flux limiter, 82
Flying Circus (FC), 294, 511, 514, 707, 709, 725
focused-beam characterization, 604
foil filter, 511, 688
foil trap, 398, 399
“forbidden” transitions, 341, 1133, 1151
Forschungszentrum Jülich, 433
Fourier propagation, 868
Fourier-transform infrared (FT-IR), 499–500
Fourier-transform method, 660, 829, 852, 867, 964, 1073
Fourier synthesis, 715
Fourier ptychography, 718
Fourier’s law, 174, 871, 874
Frantz–Nodvik equation, 785, 943, 944
Fraunhofer ILT, 386, 416, 428, 461
free–bound transitions, 481
free–free absorption, 482
free–free radiation, 481
free-electron laser (FEL), 14, 265, 593, 608, 616, 917, 961, 1031, 1040, 1068, 1075
Fresnel number, 275
frequency conversion, 853, 913, 917, 975
fringe shift, 660
full width at half maximum (FWHM), 515, 657, 659, 691, 917

Fundamental Data Working Group, 1130, 1139, 1141

GaAsP/Au Schottky diode, 695, 726
gain medium, 212, 779, 785, 801, 923, 939, 944, 951, 957, 972, 1003, 1012, 1068
gain narrowing, 944, 959, 967
gain switching, 271, 939
gas flow design, 427
gas lifetime, 810, 840
gas monitor detector (GMD), 608
gas puff target, 629, 647
gas purging, 428
gate turn-off thyristor (GTO), 807, 808
Gaunt factor, 90, 168
Gaussian beam, 56, 614
geometrical optics, 76, 77, 78, 155
geometry of laser gain media for high-power lasers, 948
Gigaphoton Inc., 9, 260, 284, 296
graphical–user interface (GUI), 424
grating-like structure, 610, 616, 618
grazing-incidence angle, 564
grazing-incidence conditions, 604, 614, 728, 1088
grazing-incidence mirror, 611, 688, 692
grazing-incidence optical elements, 604, 606
grazing-incidence optics, 540, 564, 593, 604
grazing-incidence x-ray optics (GIXO), 565–566

harmonic frequencies, 976
heat extraction, 355, 925, 948, 950, 1003
heat flux, 82
heat transport, 160, 871
heatsink, 926, 942, 950, 955, 972
Helmholtz equation, 78, 155, 190, 611
Herriot cell, 966
high-CE technology, 268
high-energy amplifier, 9223, 1003
high gain, 930, 049, 952, 1012, 1088
high-harmonic cutoff, 856
high-NA multiple patterning, 17
high net-gain, 944
high-order harmonic generation (HHG), 15
high-order harmonics, 604, 848
high-power CO_2 lasers, 17, 779, 921
high-power light source for EUV lithography based on energy recovery linac (ERL)–free-electron laser (FEL), 1065
high-power pulsed lasers, 628, 638
high-power regenerative amplifier, 968
high-power semiconductor switching device, 807
high-power ultrashort-pulse lasers for applications in EUV, x-ray generation, laser Compton scattering, and FEL, 913, 919
high repetition rate, 289, 415, 604, 611, 643, 796, 921, 961, 978, 1000
high-resolution transmission gratings, structure, and fabrication, 518
high-volume manufacturing, 71, 199, 376, 461, 480, 493, 510, 523, 539, 655, 700, 748, 760, 802, 914, 999, 1040, 1067
high-voltage breakdown, 480
higher-harmonic generation (HHG), 15, 415, 521, 848, 854, 865, 877, 886, 918, 1046
higher-order methods, 87
highly charged ion (HCI), 31, 386, 1130, 1133

hollow cathode, 384, 417
hollow-cathode-triggered pinch (HCTP), 416
  plasma, 417
holmium-based lasers, 936
  Ho:YAG laser, 978
host material, 922, 931, 949, 977
hot plasma, 28, 30, 187, 381, 395, 417, 430, 439, 490, 565, 578, 656
HULLAC code, 117, 123, 656, 664, 1196
HYDRA code, 100
hydrodynamic equations, 83, 165
hydrodynamics, 71, 83, 99, 135, 153, 197, 270
  multifluid, 88
  single-fluid, 87
hydrogen gas, 233, 311, 628, 667, 758
hydrogen plasma, 51, 628, 655, 667, 760, 767
  EUV-induced, 667
hydrogen radical and hydrogen plasma etching, 759, 760
hyper-NA, 17

i-line, 803, 1109, 1113, 1125
illumination, 35, 53, 83, 207, 262, 331, 403, 479, 485, 517, 548, 578, 590, 657, 695, 703, 714, 720, 796, 848, 868, 1046, 1118
illumination optics, 204, 239, 256, 305, 333, 510, 541, 721, 1067
image sharpness, 795
imaging region, 796
imaging reflectometry for compositional analysis, 869
imaging spectrometer, 728
implicit methods, 99
in-band emission, 43, 113, 150, 159, 176, 186, 231, 387, 415, 441, 510, 517
in-band interval, 155
in-band pulse energy, 261
in-band wavelength range, 150
induction, 331, 679, 956
industrial revolution, 788
Infineon, 450
injection lock, 801, 832, 840
injector, 288, 1040, 1054, 1075, 1080
inner-shell emission, 636, 644
inner-shell ionization, 635
in situ tin cleaning, 758
integrated coherence, 796
intensified CCD (ICCD) camera, 664
intensity distribution, 368, 401, 543, 568, 570, 588, 610, 929, 1037, 1089, 1115
intensity gain, 570, 582
interaction of intense EUV pulses with atomic and molecular gases, 627
interference lithography, 883
interference pattern, 496, 617, 874, 883
intermediate coupling, 120
intermediate focus (IF), 7
intracavity *Q*-switching, 271
intrinsic phase, 852
inverse bremsstrahlung absorption (IBA), 5
inverse Compton scattering (ICS), 919
ion acoustic wave damping, 662
ion average charge state, 270
ion-component spectrum, 662
ion density, optimum, 268
ion diagnostics, 668
ion energy distribution, charge-state-resolved, 670
ion kinetic energy distribution, 669
ionic charge-state, 656
ionization balance, 92, 93, 95

ionization energies of the first 18 stages of xenon, 1134
ionization state, 79, 99, 182, 525
ionization temperature, 125
irradiation tool, 403
irreversible changes due to intense radiation, 603
ISTEQ B.V., 10

jj coupling, 1132

k_1, 4
Kerr effect, 966
Kerr medium, 942, 943
Kerr-lens mode locking, 942, 956
kilowatt-class pre-pulse picosecond Yb:YAG laser system, 966
Kirchhoff's law, 90
Kirkpatrick–Baez optics, 579
KLA Tencor Corp., 10
KrF excimer laser, 797, 804
  thyratron-based, 804
KrF excimer laser scanner, 813
krypton (Kr), 388, 433, 629, 794, 856, 928, 1113

Lagrangian (or Eulerian) method, 85
Lambert–Beer law, 612
Langdon effect, 81
Larmor motion, 280
laser, 5, 14, 28, 54, 73, 113, 134, 161, 175, 203, 244, 271, 284, 350, 477, 521, 596, 628, 659, 779, 794, 802, 863, 912, 999
  short-wavelength, 604, 614
laser ablation, 151, 161, 607, 914
laser-assisted discharge-produced plasma (LDP), 12
  EUV sources
laser cavity, 212, 796, 926, 942, 956, 969
laser desorption, 607
laser diode, 490, 928, 934, 950, 968, 1000, 1011
laser-driven plasma, 477, 485, 527, 528
laser energy deposition, 159, 155, 183
  hybrid model, 155
  inverse-bremsstrahlung absorption coefficient, 167
  RH transport mode, 155
  H transport mode, 156
  X transport mode, 155
laser heads, 954
laser-induced damage threshold (LIDT), 926
laser interferometry, 659
laser light absorption, 121, 291
laser-discharge plasma (LDP), 350, 352, 360, 370, 378, 416, 477, 488, 491, 539
laser-driven light source, 478
laser-driven plasma source, 477
  long-term output stability, 489
laser-induced periodic surface structure (LIPSS), 616
laser interferometry, 659
laser micromachining, 966
laser platform PERLA®, 966
laser pre-pulse technology, 213, 225, 267, 308, 375
laser-produced plasma (LPP), 24–25
  sources, 27
laser-sustained plasma, 478
laser Thomson scattering, 661
Lawrence Berkeley National Laboratory (LBNL), 715, 750
leading-edge semiconductor, 804
Lehrstuhl für Lasertechnik, 416
lens stepper, 808
light recycling, 487
line broadening, 438, 481, 1197
line-center analysis module (LAM), 828

line-narrowing module (LNM), 811, 824, 832
line spectrum, 481, 1033, 1109
linear accelerator (linac), 920, 1031, 1072, 1077
liquid tin, 30, 102, 179, 190, 209, 220, 264, 305, 350
liquid tin circulation, 355
lithium (Li), 13, 976
lithographic masks, 919
lithography, 4, 43, 71, 124, 150, 199, 255, 342, 382, 432, 493, 517, 538, 603, 634, 655, 678, 747, 777, 787, 794, 848, 883, 912, 999, 1030, 1066, 1078, 1099, 1107
lobster-eye (LE) optics, 579
local thermodynamic equilibrium (LTE), 75, 115, 479
  opacity tables, 98
longitudinal acoustics waves, 877
longitudinal dispersion, 1083
longitudinal modes, 941
Lorentzian waveform, 813
Los Alamos National Laboratory, 120
low-inductance circuit, 355
low nonlinearities, 948
low-temperature plasmas driven by intense EUV pulses, 634
LPP EUV sources, 72, 152, 187, 635, 648
  integrated simulation of, 152
LS coupling, 1132
L-shell absorption edge, 597

Mach–Zender interferometer, 659
machine learning, 98, 104, 493
magnetic assist technology, 806
magnetic bearing, 798, 832
magnetic compression circuit, 816
magnetic confinement, 234, 331, 394, 710
magnetic debris mitigation, 9
magnetic field, 84, 239, 261, 280, 291, 302, 331, 426, 481, 679, 753, 914, 1033, 1040, 1068, 1093
magnetic field mitigation, 280
magnetic switch, 330, 800
magnetic trap, 428
main linac, 1077, 1081, 1085, 1096
main pulse, 33, 46, 56, 102, 135, 152, 184, 213, 225, 244, 269, 272, 309, 523, 664, 1012
mandrel, 575, 590
manufacturing and metrology in optical and x-ray regions, 575, 587
Martinez stretcher, 947
mask, 8, 205, 218, 256, 414, 450, 485, 537, 616, 713, 721, 788, 808, 867, 885, 916, 1030, 1046, 1067, 1114, 1124
mask blank, 339, 414, 434, 455, 713, 722, 1045
mask inspection, 15, 350, 369, 713, 715, 919, 1030, 1047, 1055
mask metrology, 713, 1045
mass-limited targets, 204
master oscillator (MO), 212, 271, 276, 827, 938
master oscillator–power amplifier (MOPA), 200, 271, 801, 921
material expansion, 608, 951
material removal (erosion), 605
materials damage by EUV photons and laser processing, 607
materials processing, 593, 604, 614, 779, 795
  with focused EUV/soft-x-ray pulses, HHS, and FEL, 593
Maxwell–Boltzmann statistics, 122
Maxwellian distribution, 73, 81
mean free path, 75, 84, 95, 132, 165, 174, 762, 871

mean reflectivity, 549, 554
mean time between failures (MTBF), 422, 449
mechanical properties at the nanoscale, 877
mechanical shutters, 426
megahertz pulse trains, 611
mercury-xenon lamps, 803
Metrology Light Source (MLS), 1057
metrology source, 8, 15, 17, 330, 414, 428, 480
metrology tools, 8, 14, 354, 422, 450, 479, 493, 510, 527, 576, 678, 713, 871
Michelson interferometer, 659
micro-CSM, 721
micro-/nanoprocessing, 593
micropatterning, 617
micro-roughness, 923
microscopy, 55, 339, 374, 388, 498, 519, 564, 578, 590, 608, 695, 714, 850, 868
microwave cavity resonance spectroscopy (MCRS), 665
mid-infrared (IR) light, 55, 272, 477, 548, 855, 976, 1004
mid-infrared spectral range, 976
Ministry of Economy, Trade, and Industry (METI), Japan, 819
mirror array, 961, 965, 972, 1133
Mitsubishi, 211, 261, 276, 297, 313
mode-locked thin-disk oscillators, 956
mode-locked Ti:sapphire lasers, 853
mode locking, 853, 941, 956, 967
modular design, 777, 788
molybdenum (Mo), 51, 55, 394, 405, 417, 426, 510, 543, 633, 749, 1047, 1111, 1113, 1120
momentum-changing collisions, 74
momentum spread, 1085
Monte Carlo method, 97
Moore's law, 4
MOPA scheme, 801, 938
multi-bend achromat (MBA), 1032, 1039, 1055
multiblock grid/mesh, 86, 100
multiconfiguration Dirac–Fock (MCDF) code, 1196
multiconfiguration Hartree–Fock (MCHF) code, 1196
multi-foil collector, 631
multi-foil mirror, 580
multi-foil optics (MFO), 564
multilayer mirror, 7, 28, 48, 113, 262, 334, 340, 353, 392, 429, 441, 460, 510, 511, 616, 634, 644, 656, 667, 685, 691, 724, 749, 761, 1066, 1088, 1098
multilayer mirror (MLM) exposure to hydrogen plasma, 767
multi-line operation, 272
multi-pass amplifier architecture, 962, 967, 972
multi-pass amplifier Fourier transform architecture, 964
multi-pass amplifier nearly collimated beam propagation (NCBP) scheme, 962, 972
multi-pass amplifier relay imaging architecture, 962
multi-pass amplifiers, 274, 945, 956, 961, 978
multi-pass regenerative FEL amplifier (RAFEL), 1070, 1073
multi-turn energy-recover linac, 1096
multiple amplifying paths, 781
multiple-exposure lithography, 804
multiple patterning (MP), 16
multiple-shot exposure, 611, 615
multiplexing, 404, 920, 945, 961
multiply charged ions, 112, 115, 635
multiply excited states, 34, 89, 115, 122, 131

multi-pulse extraction (MPE), 1002, 1005, 1016

nanolithography, 112, 134, 510, 525
nanometrology applications, 493
nanopatterning, 604
  of solids, 614
National Institute of Standards and Technology (NIST), 29, 437, 512, 678
Navier–Stokes equations, 84
Nb_3Sn, 1091
Nd:YAG laser, 28, 35, 45, 73, 113, 121, 134, 157, 177, 284, 291, 350, 360, 525, 629, 708, 913, 923
  for pre-pulse
Nd:YAG-laser-produced plasma source, 525
N-doping, 1091
nearly collimated beam propagation (NCBP) scheme, 962, 965, 972
neodymium-doped yttrium aluminum garnet (Nd:YAG), 28
neon, 342, 389, 422, 433, 637, 857
net gain, 959
neural network, 98
New Energy and Industrial Technology Department Organization (NEDO), 257, 276, 297
NewSubaru, 681, 721
NIST reflectometer chamber, 697
nitrided Si photodiode, 703
nitrogen, 48, 237, 339, 388, 425, 447, 647, 756, 1091
noble gas halides, 794
non-collective scattering, 662
nondiffusive thermal transport, 872
non-Gaussian beams, 614
nonlinear phonon relaxation, 953
nonlinear refractive index, 924
non–local thermodynamic equilibrium (NLTE), 75, 89, 92, 97, 121
  plasmas, 100
non-telecentricity, 713
nonthermal ablation threshold, 612
nonthermal solid-to-solid phase transition, 608
nonthermally ablated layer, 614
normal-incidence collector optics, 537
  for EUV sources, 537
normal-incidence conditions, 604
normal-incidence optical elements, 604
Nomarski microscopy, 608
numerical aperture (NA), 4
numerical simulation, 284, 644, 799, 836, 1070

off-axis parabolic (OAP) mirror, 485
opacity, 32, 42, 99, 119, 130, 157, 176, 284, 1134
operator splitting, 99
operation frequency, 7
optical cavity, 797, 944
optical depth, 32, 78, 95, 115, 134, 136, 172
optical element, 351, 382, 398, 425, 512, 538, 564, 604, 683, 719, 728, 963, 973
  surface damage, 965
optical parametric amplifier (OPA), 920, 976, 1005
optical parametric chirped-pulse amplification (OPCPA), 918
optical parametric generator (OPG), 976
optical path difference (OPD), 926
optical projection lithography, 4
optical system, hybrid, 586
optical thickness, 150, 161, 180, 659

optically pumped CO_2 laser, 921
optics and detectors for EUVL, 691
optics design rules and ray tracing, 571, 582
optics geometry, 567
  ellipsoidal 568
  parabolic 567
optimum laser pulse duration, 33
optimum pre-pulse duration, 34
oscillator strength, 36, 88, 117, 131
out-of-band (OOB) light, 517, 540, 826
out-of-band (OOB) power, 7
out-of-band (OOB) radiation, 113, 228, 450, 497, 681,725, 759, 858
  suppression, 439, 460
output coupler (OC), 821, 942, 958
oxidation, 685, 704, 750, 763, 858, 1120
oxide charging by photoelectrons, 703
oxygen (O), 47, 338, 388, 422, 642, 690, 704, 767, 821

parabolic mirror, 581, 683, 954
parasitic seeding, 272
parasitic oscillation, 275, 787, 930
particle acceleration, 934, 952
partition function factor, 116, 132
Paschen's curve, 417
Paschen's law, 418, 1118
Paul Scherrer Institute (PSI), 414, 679
$PbWO_4$, 612
PbI_2, 612
peak current, 350, 383, 417, 489, 800, 1071, 1094
peak intensity, 30, 231, 366, 402, 496, 797, 853, 865, 925, 945, 963, 1087, 1115
pedestal, 214, 272, 290, 865, 974
phase matching, 853
phase shift, 659, 868, 1085
phase space, 95, 1031, 1052, 1071, 1083
phase transition, 155, 190, 608, 975
Philips EUV GmbH, 417
photodiode, 334, 359, 385, 415, 443, 492, 510, 643, 685, 694, 702, 710, 730, 811, 860
photodiode array monitors, 811
photoionization, 5, 124, 481, 608, 628, 635, 889, 1134
photoionization cross-section, 1135
photoionized plasmas, 627, 637, 647
photon distribution, 76, 91
photon phase space distribution function, 95
Physikalische-Technische Bundesanstalt (PBT), 353, 434, 455, 512, 678, 683, 700, 724
picosecond pulses, 912, 921, 932, 950, 961, 975, 1001
pinch effect, 11, 360
pinch plasma, 363, 384, 402, 436
  hollow-cathode triggered (HCT), 12, 383
  pinch condition, 436
Planck function, 90, 136
Planck's law, 439
plasma, 5, 17, 28, 73, 112, 131, 150, 199, 203, 256, 285, 330, 350, 428, 477, 539, 627, 647, 655, 760, 1129, 1197
plasma-based lasers, 604, 617
plasma current, 291, 331
plasma debris and its mitigation, 30, 233, 280, 312, 398
plasma diagnostics, 655
plasma emission spectra, 635, 644
plasma frequency, 6, 73, 96, 659
plasma implosion, 360
plasma instability, 188
plasma kinetics code, 121
plasma opacity, 285

plasma properties, 73, 90, 541
Pockels cell, 939, 959, 968
Pohang Accelerator Laboratory (PAL), 724
polarization dependence in mirror reflectance, 696
polarized electric field, 80
polymer chain scissions, 606
poly(methyl methacrylate) (PMMA), 595, 616
ponderomotive energy, 850
population distribution function, 116
population inversion, 635, 795, 927, 939, 949
post-compression, 913, 978
  of ultrashort pulses, 966
power amplifier (PA), 213, 275, 801, 827, 921, 938, 943, 960, 1006
power requirements, 6, 14, 202, 557, 692, 826, 1049
power scaling, 210, 225, 264, 307, 416, 539, 956, 978, 1038
pre-ionization, 818
pre-pulse, 9, 33, 51, 101, 151, 187, 200, 213, 225, 244, 264, 280, 293, 308, 523, 656, 913, 959, 966, 1012
pre-pulse laser, 35, 51, 101, 267, 284, 293, 375, 664, 913, 959
  technology, 210, 267, 308, 375
primary source standards, 679
prisms, 86, 640, 797, 824, 942
programmable logic controller (PLC), 422
projection exposure, 1114, 1123
projection mirror, 510
projection optics, 202, 256, 510, 537, 548, 684
proximity exposure, 1123
PTB soft-x-ray radiometry beamline, 684
PtSi Schottky-barrier diodes, 696
ptychography, 718, 867
pulse compression, 807, 865, 948, 973
  chirped volume Bragg grating (CVBG), 947, 973
  dielectric grating, 971
pulse duration, 28, 33, 47, 137, 160, 187, 267, 298, 350, 361, 383, 393, 512, 521, 629, 658, 669, 796, 801, 814, 832, 853, 863, 877, 887, 914, 925, 934, 941, 956, 977, 1003, 1032
pulse length, 33, 54, 134, 512, 606, 916, 941, 1076
pulse power module (PPM), 814
pulse stretching, 817, 946
pulse-to-pulse energy stability, 808, 914
pulsed high current, 357
pulsed power circuit, 794, 805, 840
pump cavity, 954
pump chamber, 968
pump diodes, 924, 949, 960, 972
pump head, 954, 972
purge gas, 428, 444
PZT (fine) actuators, 828

Q-switching, 271, 939
Q-value, 1078, 1091
quadrupole magnets, 1081
quantum cascade laser (QCL), 272
quantum defect, 864, 928, 953, 977, 1006
quasi-Moseley's law, 41
quasi–phase matching, 857
quasi-three-level system, 932

radiation damage, 604, 608, 703, 1095
radiation-dominated (RD) laser-ablation fronts, 151, 170
  1D boundary conditions, 161, 336

boundary-value problem, 161, 173
Chapman–Jouget regime, 163
numerical profiles, 163
qualitative structure, 150
scaling laws, 151, 161, 167
semi-analytical treatment, 152, 164
radiation-dominated (RD) plasma, 151, 161
radiation field, 75, 95, 126, 151, 189, 645
radiation-hydrodynamic (RH) code, 72, 83, 93, 99
radiation-hydrodynamic (RH) modeling, 71, 129
radiation-hydrodynamic (RH) simulations, 72, 92, 126, 135
radiation transport/transfer, 95, 122, 151, 190, 285
equation, 84, 96, 125, 171
in plasma, 480
radiative emission, 88, 93, 389
radiative properties, 89, 181, 645
radiative rate, 91, 189
radiofrequency (RF) accelerator, 1073
RADIOM model, 125
Raizer, Yu., 477, 483
RALEF-2D code, 151, 153
rate matrix, 91, 125
Rayleigh range, 223
Rayleigh's criterion, 4, 53
Rayleigh's equation, 1108
raytracing, 76, 100, 567, 570, 582
reaction microscope, 890
recirculation loop, 1076
recollision, 848
reflectance, 43, 227, 262, 310, 441, 455, 461, 543, 685, 691, 679, 700, 728, 860, 869
reflective/refractive optical elements, 608
reflective coating, 231, 310, 552
refraction, 76, 96, 155, 177, 490, 544, 564, 749, 853, 1003
refractive index, 17, 76, 90, 490, 544, 565, 612, 656, 780, 795, 834, 853, 924, 950
regenerative amplifiers, 940, 951, 960, 972
requirements sources for mask defect metrology tools, 8
requirements for next-generation wafer inspection (non-actinic) tools, 17
source wavelength, 17
bandwidth, 17
source étendue, 17
brightness, 17
energy stability, 17
pulse repetition rate, 17
duty cycle, 17
radiation-hydrodynamic
requirements for optical wafer inspection metrology tools, 17
defect sensitivity, 17
throughput (unpatterned), 17
throughput (patterned), 17
availablilty, 17
RESCAN, 719
Research Instrument (RI), 13, 416
resonance absorption, 80
resonance frequency, 665
resonance transitions, 13, 29, 43, 112, 121, 139
response linearity, 512, 705
reticle, 205, 510, 680, 715, 721, 1114, 1124
RF CO_2 laser, 1016
ring cavity, 960, 970
rod-type gain medium, 948
roof reflectors, 954
rotating disk electrodes, 540
rotationally symmetric GIXO, 566, 590

roughness (RMS), 615, 969, 977
RWTH Aachen University, 416
RZLINE code, 285

SACLA, 615
Saha equation, 90, 126
Saha–Boltzmann distribution, 75, 90
Saha–Boltzmann equilibrium, 75
SASE-FEL, 1068, 1070, 1100
saturable absorber, 936, 956
saturation effects under pulsed irradiation, 708
saturation energy, 709, 939
saturation parameter, 709
scaling factors, 120
scanner interface, 243
scanning white light interferometry (SWLI), 496
scatterometry, 479, 493, 681, 715, 872, 879
Schlieren-measured data, 799
Schmidt arrangement, 579
seed wavelength, 273
self-amplified spontaneous emission (SASE), 265, 606, 916, 1067, 1070
self-calibration, 702
self-diagnostic system, 831
self-focusing, 183, 925, 949, 959
self-phase modulation, 925, 958
semiconductor HVM, 265, 804, 840
semiconductor metrology, 482, 493, 497
semiconductor saturable absorber mirror (SESAM), 942, 956
serial resistance, 707
sextupole magnets, 1034, 1084
shadowgraph, 225, 269, 286, 309, 656, 669
SHARP microscope, 715
shock wave, 31, 87, 224, 798, 833
short-wavelength laser, 604, 614
shorter-wavelength sources, 43
shorter-period undulators, 1093
shot noise, 455, 1067
side-pumped laser, 929
side pumping, 948
silicon (Si), 488, 510, 543, 583, 593, 612, 643, 684, 694, 702, 712, 749, 761, 858, 876, 955, 1047, 1066, 1108
silicon carbide, 396, 995
Si/Mo multilayer, 616
simulation, 72, 85, 92, 104, 121, 135, 152, 175, 187, 270, 284, 285, 360, 494, 564, 582, 588, 628, 644, 661, 785, 836, 850, 1000, 1016, 1053, 1078, 1085, 1118
single-multipole approximation, 1196
single-pass SASE, 1070
single-pass self-seeding FEL, 1070
SiriusXT microscope, 55
slab gain medium, 951
slab-waveguide diffusion-cooled geometry, 275
smart energy, 778
smart manufacturing, 778
smart mobility, 788
S_n method, 154
Sn VII, Sn VIII, Sn IX, Sn X, and Sn XI, 1197
Sn plasma spectra, 1197
soft-x-ray photons, 628
soft-x-ray radiation, 918
software packages, 568
solid-state 2-μm laser drivers, 999
solid-state lasers, 14, 134, 271, 525, 789, 911, 999
solid-state pulsed power circuit (SPC), 805
solid-state pulsed power module (SSPPM), 804
source
  low-peak-power, 605

high-peak-power, 606
source collector module, 400, 539, 550
source étendue, 7, 208, 263, 542
source function, 95, 154
sources for beyond EUV lithography (BEUVL), 43, 56
sp^3-to-sp^2 conversion, 608
space charge effects, 1080
spatial instability, 489
specific intensity, 95
spectator electron, 89
spectral analysis module (SAM), 828
spectral absorption coefficient, 154
spectral broadening, 134, 483, 919, 966, 1116
spectral content, 202, 207, 228
spectral filter, 231, 305, 400, 441, 456, 518, 549, 725
spectral opacities, 155
spectral purity, 71, 29, 47, 113, 134, 175, 206, 680, 690, 820, 1073
spectral purity filter (SPF), 8, 430, 441, 549
spectral radiance, 136, 478, 485
spectral reflectometry, 453
spectral resolution, 434, 453, 488, 518, 664, 728
spectroscopic reflectometry (SR), 479, 488
spectroscopic ellipsometry (SE), 479, 488, 495
spectroscopy, 150, 272, 283, 479, 498, 517, 520, 563, 580, 590, 617, 635, 640, 665, 767, 871, 890, 1004, 1142, 1162
specular spectroscopic scatterometry, 494
sputter rate, 374, 395
sputter yield, 395
sputtering, 280, 302, 331, 373, 391, 426, 484, 668, 710, 752, 767, 814
stability for high radiation, 695, 710
standing-wave cavity, 960, 970
STAR code, 185
stannane, 234, 281, 312, 710, 758
steady-state approximation, 78, 92, 126, 160, 176
Stefan–Boltzmann law, 150, 1122
stochastic effect, 202, 1067, 1098
storage rings for metrology applications, 679
storage ring lattice, 1035, 1047
stray light reduction, 664
super-high-pressure mercury lamps, 1107, 1114, 1125
superconducting radiofrequency accelerator, 1073, 1090
SUPERSTRUCTURE (atomic code), 1196
surface acoustic waves, 878
surface contamination, 612, 685
surface scattering, 551
synchrotron radiation, 678, 703, 714, 1034, 1042, 1076, 1084, 1100
synchrotron radiation, physics of, 1032
synchrotron-radiation metrology for EUV source applications, 696
synchrotron radiation sources, 604, 679, 695, 1030, 1040
Synchrotron Ultraviolet Radiation Facility (SURF), 678, 681
system integration, 724
system qualification, 539, 554

Talbot effect, 617
TEA CO_2 laser, 921
temporal chirp, 946
temporal measurements, 643
temporal stability, 336, 490, 685
Tesla Test Facility Free-Electron Laser, Phase 1 (TTF1 FEL), 616

Test EUVL (TEUVL) tool, 450
thermal conductivity, 165, 237, 351, 394, 551, 757, 925, 1025, 1123
thermal deformation, 278, 290, 963
thermal distribution, 75, 81
thermal expansion coefficient, 926
thermal gradient, 925, 951, 1002
thermal lensing, 926, 943, 959
thermal plasma, 478, 479
thermal shock resistance, 926
thermal transport, 81, 100, 871
thermally induced OPD, 852, 1007
thermomechanical processes, 613
thermo-optic coefficient, 926, 952, 978, 1007
THERMOS code, 156
thin-disk amplifiers, 934, 956
thin-disk laser technology, 918, 978
thin-disk lasers, 922, 931, 945, 951, 960, 977, 1002
thin-disk multi-pass amplifiers, 951, 961
thin-disk regenerative amplifiers, 958
thin-disk oscillators, 942
Thomson parabola, 670
Thomson scattering, 270, 285, 661
throughput, 6, 17, 202, 218, 258, 287, 455, 488, 496, 510, 539, 558, 691, 714, 748, 796, 813, 865, 885, 919, 1040, 1122
thulium (Tm), 922, 935, 977, 1004
thulium lasers, 11, 934, 978
thyratron, 799, 806
time-of-flight (TOF), 668
tin (Sn), 200, 220, 234, 306, 510, 525, 748
tin bath, 12, 350
tin delivery systems, 220
tin droplets, 161, 175, 209, 220, 243, 265, 288, 305, 358, 541, 556, 787, 913, 959, 975
tin fuel, 5, 220, 306, 351, 754
tin ions, 13, 113, 313, 668, 710
  fundamental atomic data for, 13
  multiply charged, 112, 138
tin management, 239
tin plasma, 71, 113, 122, 131, 165, 260, 285, 293, 313, 521, 662, 885, 914
  CO_2 laser produced, 260
titanium-doped sapphire, 850
Ti:sapphire, 45, 521, 657, 850, 863, 913, 923, 934, 1001
Tm:YLF, 936, 1000, 1007
  laser properties, 1007
total external reflection, 566, 856
transient absorption spectroscopy, 890
transition energies, 88, 339, 1130
transmission grating spectrometer, 510, 517
transmission mask, 452, 617
transverse gas flow, 781, 788
Treacy compressor, 946
TRIM software, 399
troubleshooting, 831
tungsten (W), 41, 394, 405, 482, 493, 664, 760, 1111, 1123
twin-chamber excimer laser, 805
twin-chamber technology, 800
two-color laser irradiation, 152
  CE optimization strategy, 175, 185
  master laser, 180
  optimized density profiles, 177, 185
  optimized steady-state CE
    results of optimization, 185
  slave laser, 152, 175, 186
  transient peak of CE, 185

U49 undulator, 684
ultra-narrow seed laser, 820
ultrashort-pulse lasers, 913, 977
ultrashort pulses, 608, 925, 940, 952, 966, 978, 1004

ultraviolet (UV), 112, 256, 301, 414, 478, 497, 548, 564, 603, 627, 638, 688, 794, 850, 928, 999, 1066, 1113, 1125
ultraviolet lamps for lithography, 1107
uncertainty quantification, 104
undulator system, 1078, 1084
undulator tapering, 1085
undulators, 1036, 1056, 1084, 1093
unresolved transition array (UTA), 29, 42, 1139
unstable resonator, 821

vacuum seal, 355, 431
vacuum spark, 12, 1195, 1202
vacuum ultraviolet (VUV), 478, 548
velocity-map imaging, 890

wafer inspection, 15
wall cooling, 780
wall-plug-to photon conversion efficiency, 11
warm dense matter (WDM), 604
water window
  imaging in, 53
  microscope illuminator, 329, 338
  sources, 18, 47
wavelength
  calibration, 437, 455, 728, 1198
  reduction, 4, 18
wavemeter, 811
wavenumber vector, 662
white light interferometry, 493
Wien's displacement law, 439
wiping mechanism, 354
Wolter-type optics, 569, 581

x-ray, 47, 155, 334, 381, 415, 510, 530, 547, 563, 575, 580, 588, 593, 604, 627, 662, 679, 702, 720, 850, 870, 912, 920, 934, 976, 1030, 1040, 1056, 1073
  applications, 913, 921, 976
  backlighting, 630
  sources, 563, 605, 627, 679, 912, 978, 1000
  optical systems, 563, 582
  optics, 564, 580
xenon (Xe), 5, 10, 13, 284, 330, 383, 396, 404, 417, 425, 432, 442, 480, 539, 583, 636, 794, 856, 928, 1113, 1129
  emission spectrum, 387, 434
  ions, fundamental data for, 13
  plasma, 331, 419
  spectra, 437, 1132
XeCl laser, 794
XeF excimer laser, 795
XE LPP, 10

Yb:fiber lasers, 863
Yb:LuAG, 933, 943, 968
Yb:YAG laser, 966
Young's modulus, 879, 880, 928
yttrium-aluminum garnet (YAG), 931

Z-pinch, 11, 329, 351, 362, 436, 511, 563, 628, 756, 885
  electrode-less, 329
  inductive, 329
zig-zag configuration, 951